S/N 08/903,486 PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Leonard Forbes et al.

Examiner: W. Mintel

Serial No.:

08/903,486

Group Art Unit: 2811

Filed:

July 29, 1997

Docket: 303.326US1

Title:

SILICON CARBIDE GATE TRANSISTOR

SUPPLEMENTAL COMMUNICATION CONCERNING CO-PENDING APPLICATION(S)

Assistant Commissioner for Patents Washington, D.C. 20231



Applicant would like to bring to the Examiner's attention the following related copending application(s) for the above-identified patent application:

4	Sp	V	V	1

	Serial No. 09/259,870	Filing Date 03/01/1999	Attorney Docket 00303.326US2	Title SILICON CARBIDE GATE TRANSISTOR AND FABRICATION PROCESS
	08/902,843	07/29/1997	00303.354US1	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
	09/135,413	08/14/1998	00303.354US2	METHOD FOR OPERATING A DEAPROM HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR
	09/134,713	08/14/1998	00303.354US3	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
	09/140,978	08/27/1998	00303.355US2	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
•	08/903,452	07/29/1997	00303.324US1	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
•	09/256,643	02/23/1999	00303.324US2	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
	09/138,294	08/21/1998	00303.353US2	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE

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COMMUNICATION CONCERNING CO-PENDING APPLICATIONS

Serial Number: 08/903,486 Filing Date: July 29, 1997

Title: SILICON CARBIDE GATE TRANSISTOR

Page 2 Dkt: 303.326US1

JIM,	09/141,392	08/27/1998	00303.355US3	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
	08/902,133	07/29/1997	00303.356US1	DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE
	08/903,453	07/29/1997	00303.378US1	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
MM	09/258,467	02/26/1999	00303.378US2	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS

Respectfully submitted,

LEONARD FORBES ET AL.

By Applicant's Representatives,

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Reg. No. 35/271

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Assistant Commissioner of Patents, Washington, D.C. 20231 on August 30, 1999.

JONATHAN FERGUSON

Name

Signature

Gp 28/1



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Assistant Commissioner for Patents Washington, D.C. 20231

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We are transmitting herewith the following attached items (as indicated with an "X"):

- X A return postcard.
- X A Supplemental Information Disclosure Statement with authorization to charge the fee of \$240.00 as required under 37 C.F.R. §§ 1.97(c) and 1.17(p) to Deposit Account No. 19-0743 (1 p.), Form 1449 (1 p.), and copies of 2 cited references.
- A Communication Concerning Copending Applications (2 p.). X

Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this Transmittal Letter and the paper, as described above, are being deposited in the United States Postal Service, as first class mail, in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on this 30 day of August, 1999.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

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Atty: Robert E. Mates Reg. No. 35,271

Customer Number 21186

(GENERAL)